

**Amendments to the Specifications:**

**In the Title**

Change the Title to:

Multijunction Solar Cell with a Bypass Diode having an Intrinsic Layer

**On page 2:**

Please replace the amended paragraph that begins a line 2, page 1 of the present application with the following amended paragraphs:

This application is a continuation application of U.S. Patent Application Serial No. 10/280,593, filed on October 24, 2002, now U.S. Patent No. \_\_\_\_\_, which is a continuation-in-part of Application Serial No. 09/999/598, filed on October 24, 2001, now U.S. Patent No. 6,680,432.

This application is also related to co-pending U.S. Patent Application Serial No. 10/723,456 filed November 26, 2003, which is a continuation application of U.S. Application Serial No., 09/999,598, filed October 24, 2001, now U.S. Patent No. 6,680,432.

This application is also related to co-pending U.S. Patent Application Serial No. 10/336,247 filed January 3, 2003, which is a continuation application of U.S. patent application Ser. No. 09/934,221, filed on August 21, 2001, now U. S. Patent No. 6,600,100, which is a division of U.S. patent application Ser. No. 09/314,597, filed on

May 19, 1999, now U.S. Pat. No. 6,278,054, which claims priority from U.S. provisional patent application Ser. No. 60/087,206, filed on May 28, 1998. U.S. application Ser. No. 09/753,492, filed January 2, 2001, now U.S. Pat. No. 6,359,210, is also a division of Ser. No. 09/314,597.

**On page 26, in the Abstract, cancel lines 2-10 and substitute:**

A multijunction solar cell, including first and second solar cells on a substrate with a bypass diode having an intrinsic layer and operative for passing current when the multijunction solar cell is shaded. In one embodiment, a vertical sequence of solar cells are epitaxially grown on a first portion of the substrate, and the layers of the diode are epitaxially grown on a second portion of the substrate with the layers of the bypass diode being deposited subsequent to the layers of the top solar cell.